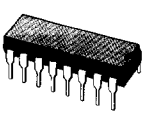
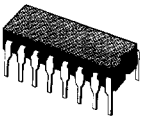
8 BIT SHIFT REGISTER WITH OUTPUT LATCHES (3 STATE)

- HIGH SPEED
  f_{MAX} = 55 MHz (TYP.) AT V_{CC} = 5 V
- LOW POWER DISSIPATION
  I_{CC} = 4 μA (MAX.) AT T_A = 25 °C
- HIGH NOISE IMMUNITY
  $V_{NIH} = V_{NIL}$ = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
  15 LSTTL LOADS FOR QA TO QH
  10 LSTTL LOADS FOR QH'
- SYMMETRICAL OUTPUT IMPEDANCE
  $|I_{OH}| = I_{OL}$ = 6 mA (MIN.) FOR QA TO QH
  $|I_{OH}| = I_{OL}$ = 4 mA (MIN.) FOR QH'
- BALANCED PROPAGATION DELAYS
  $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
  V_{CC} (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE
  WITH LSTTL 54/74LS595



B1R
(Plastic Package)



F1R
(Ceramic Package)

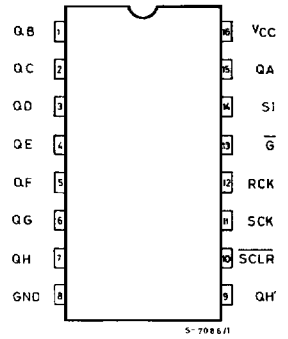
M1R
(Micro Package)

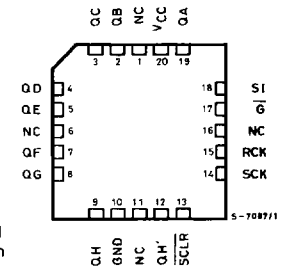
C1R
(Chip Carrier)

ORDER CODES :

M54HC595F1R M74HC595M1R
M74HC595B1R M74HC595C1R

PIN CONNECTIONS (top view)





NC =
No Internal
Connection

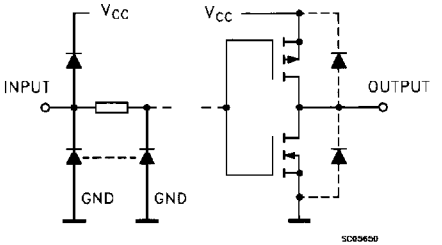
DESCRIPTION

The M54/74HC595 is a high speed CMOS 8-BIT SHIFT REGISTERS/OUTPUT LATCHES (3-STATE) fabricated in silicon C^2MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. This device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. The storage register has 8 3-STATE outputs. Separate clocks are provided for both the shift register and the storage register.

The shift register has a direct-overriding clear, serial input, and serial output (standard) pins for cascading. Both the shift register and storage register use positive-edge triggered clocks. If both clocks are connected together, the shift register state will always be one clock pulse ahead of the storage register.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT

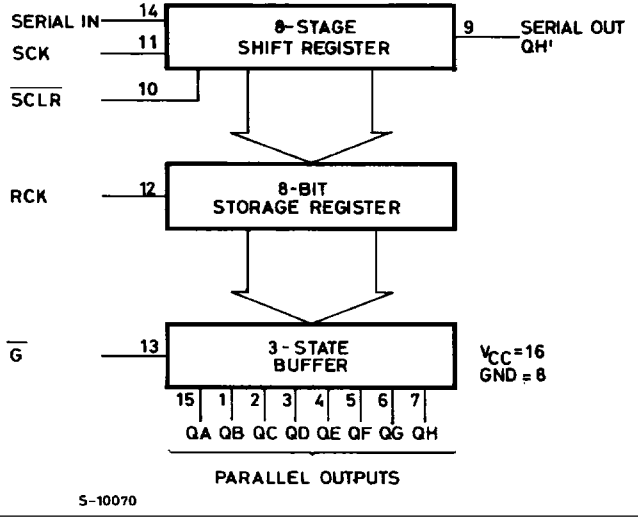


TRUTH TABLE

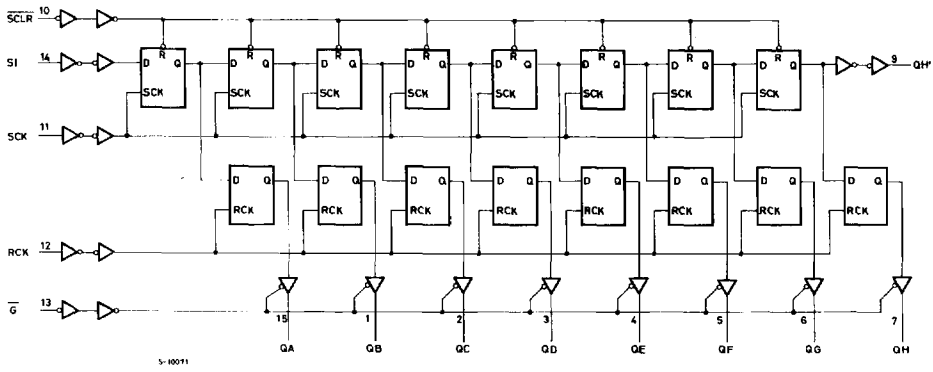
INPUTS					OUTPUT
SI	SCK	$\overline{SCLR}$	RCK	$\overline{G}$	
X	X	X	X	H	QA THRU QH OUTPUTS DISABLE
X	X	X	X	L	QA THRU QH OUTPUTS ENABLE
X	X	L	X	X	SHIFT REGISTER IS CLEARED
L	⌐	H	X	X	FIRST STAGE OF S.R. BECOMES "L" OTHER STAGES STORE THE DATA OF PREVIOUS STAGE, RESPECTIVELY
H	⌐	H	X	X	FIRST STAGE OF S.R. BECOMES "H" OTHER STAGES STORE THE DATA OF PREVIOUS STAGE, RESPECTIVELY
X	⌙	H	X	X	STATE OF S.R IS NOT CHANGED
X	X	X	⌐	X	S.R. DATA IS STORED INTO STORAGE REGISTER
X	X	X	⌙	X	STORAGE REGISTER STATE IS NOT CHANGED

X: DON'T CARE

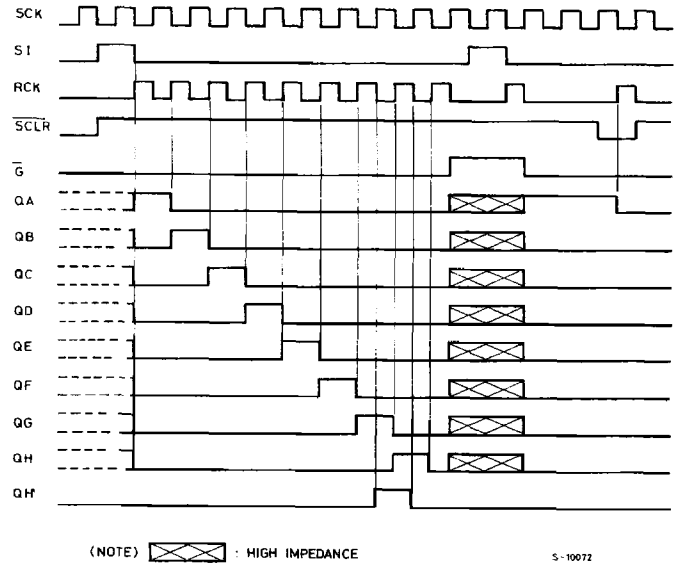
LOGIC DIAGRAM



LOGIC DIAGRAM



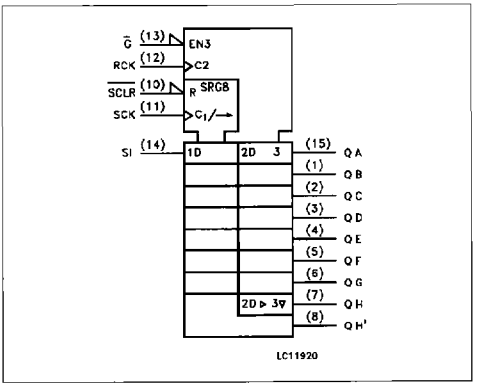
TIMING CHART



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 2, 3, 4, 5, 6, 7, 15	QA to QH	Data Outputs
9	QH'	Serial Data Outputs
10	$\overline{SCLR}$	Shift Register Clear Input
11	SCK	Shift Register Clock Input
13	$\overline{G}$	Output Enable Input
14	SI	Serial Data Input
12	RCK	Storage Register Clock Input
8	GND	Ground (0V)
16	V_{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current Per Output Pin QA-QH	± 35	mA
I_O	DC Output Current Per Output Pin QH'	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 70	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.
(*) 500 mW: ≅ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature: **M54HC** Series **M74HC** Series		-55 to +125 -40 to +85	°C °C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2 V	0 to 1000	ns
		V_{CC} = 4.5 V	0 to 500	
		V_{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions			Value							Unit
		V_{CC} (V)			T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0			1.5			1.5		1.5		V
		4.5			3.15			3.15		3.15		
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	2.0					0.5		0.5		0.5	V
		4.5					1.35		1.35		1.35	
		6.0					1.8		1.8		1.8	
V_{OH}	High Level Output Voltage (for QH' output)	2.0	V_I = V_{IH} or V_{IL}	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I_O=-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I_O=-5.2 mA	5.68	5.8		5.63		5.60		
V_{OH}	High Level Output Voltage (for QA to QH outputs)	2.0	V_I = V_{IH} or V_{IL}	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I_O=-6.0 mA	4.18	4.31		4.13		4.10		
		6.0		I_O=-7.8 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage (for QH' output)	2.0	V_I = V_{IH} or V_{IL}	I_O= 20 µA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I_O= 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I_O= 5.2 mA		0.18	0.26		0.33		0.40	
V_{OL}	Low Level Output Voltage (for QA to QH outputs)	2.0	V_I = V_{IH} or V_{IL}	I_O= 20 µA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I_O= 6.0 mA		0.17	0.26		0.33		0.40	
		6.0		I_O= 7.8 mA		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	V_I = V_{CC} or GND				±0.1		±1		±1	µA
I_{OZ}	3 State Output Off State Current	6.0	V_I = V_{IH} or V_{IL} V_O = V_{CC} or GND				±0.5		±5		±10	µA
I_{CC}	Quiescent Supply Current	6.0	V_I = V_{CC} or GND				4		40		80	µA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

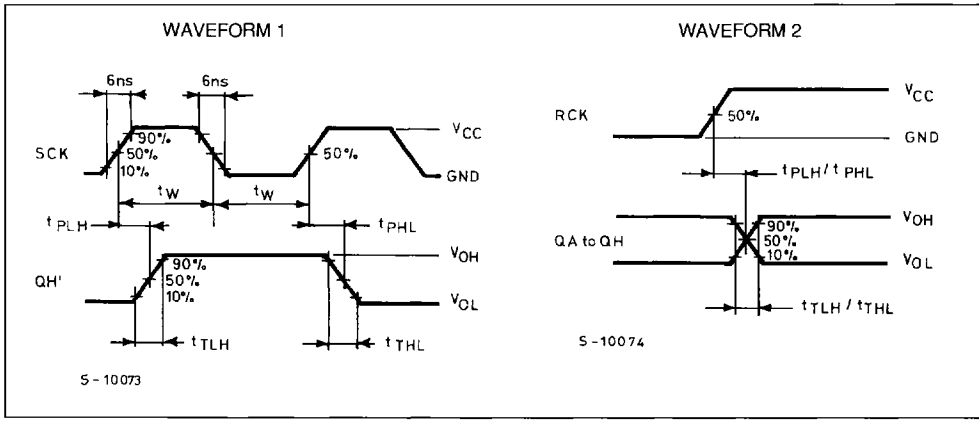
Symbol	Parameter	Test Conditions			Value							Unit
		V_{CC} (V)	C_L (pF)		T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time (Qn)	2.0	50			25	60		75		90	ns
		4.5				7	12		15		18	
		6.0				6	10		13		15	
t_{TLH} t_{THL}	Output Transition Time (QH')	2.0	50			30	75		95		115	ns
		4.5				8	15		19		23	
		6.0				7	13		16		20	
t_{PLH} t_{PHL}	Propagation Delay Time (SCK - QH')	2.0	50			45	125		155		190	ns
		4.5				15	25		31		38	
		6.0				13	21		26		32	
t_{PLH} t_{PHL}	Propagation Delay Time ($\overline{SCLR}$ - QH')	2.0	50			60	175		220		265	ns
		4.5				18	35		44		53	
		6.0				15	30		37		45	
t_{PLH} t_{PHL}	Propagation Delay Time (RCK - Qn)	2.0	50			60	150		190		225	ns
		4.5				20	30		38		45	
		6.0				17	26		32		38	
		2.0	150			75	190		240		285	ns
		4.5				25	38		48		57	
		6.0				22	32		41		48	
t_{PZL} t_{PZH}	3 State Output Enable Time	2.0	50	R_L = 1 KΩ		45	135		170		205	ns
		4.5				15	27		34		41	
		6.0				13	23		29		35	
		2.0	150	R_L = 1 KΩ		60	175		220		265	ns
		4.5				20	35		44		53	
		6.0				17	30		37		45	
t_{PLZ} t_{PHZ}	3 State Output Disable Time	2.0	50	R_L = 1 KΩ		30	150		190		225	ns
		4.5				15	30		38		45	
		6.0				14	26		32		38	
f_{MAX}	Maximum Clock Frequency	2.0	50		6.0	17		4.8		4		ns
		4.5			30	50		24		20		
		6.0			35	59		28		24		
		2.0	150		5.2	14		4.2		3.4		ns
		4.5			26	40		21		17		
		6.0			31	45		25		20		
$t_{W(H)}$	Minimum Pulse Width (SCK, RCK)	2.0	50			17	75		95		110	ns
		4.5				6	15		19		22	
		6.0				6	13		16		19	
$t_{W(L)}$	Minimum Pulse Width ($\overline{SCLR}$)	2.0	50			20	75		95		110	ns
		4.5				6	15		19		22	
		6.0				6	13		16		19	
t_s	Minimum Set-up Time (SI - CCK)	2.0	50			25	50		65		75	ns
		4.5				5	10		13		15	
		6.0				4	9		11		13	

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

Symbol	Parameter	Test Conditions			Value							Unit
		V_{CC} (V)	C_L (pF)		T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_s	Minimum Set-up Time (SCK - RCK)	2.0	50			35	75		95		110	ns
		4.5				8	15		19		22	
		6.0				6	13		16		19	
t_s	Minimum Set-up Time ($\overline{SCRL}$ - RCK)	2.0	50			40	100		125		145	ns
		4.5				10	20		25		29	
		6.0				7	17		21		25	
t_h	Minimum Hold Time	2.0	50				0		0		0	ns
		4.5					0		0		0	
		6.0					0		0		0	
t_{REM}	Minimum Clear Remuval Time	2.0	50			15	50		65		75	ns
		4.5				3	10		13		15	
		6.0				3	9		11		13	
C_{IN}	Input Capacitance					5	10		10		10	pF
C_{PD} (*)	Power Dissipation Capacitance					184						pF

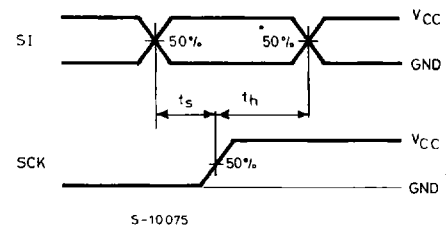
(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

SWITCHING CHARACTERISTICS TEST WAVEFORM



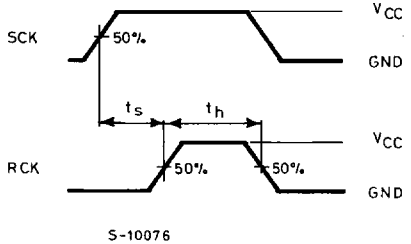
SWITCHING CHARACTERISTICS TEST WAVEFORM (continued)

WAVEFORM 3



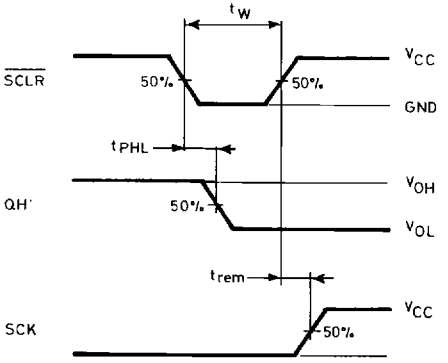
S-10075

WAVEFORM 4



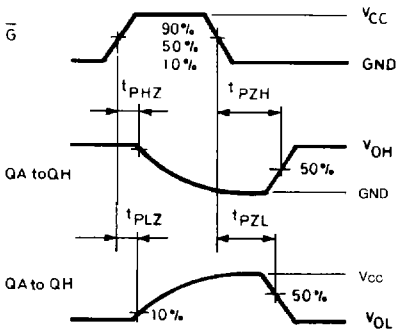
S-10076

WAVEFORM 5



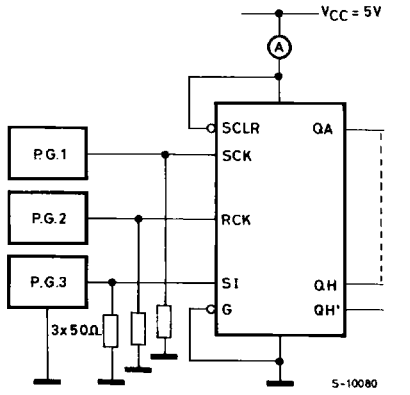
S-10077

WAVEFORM 6



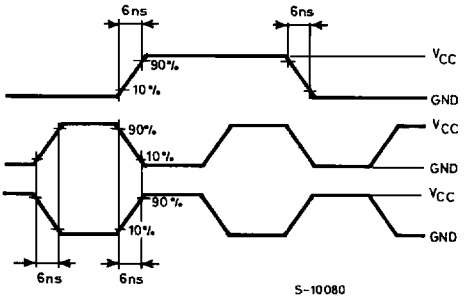
S-10078

TEST CIRCUIT I_{CC} (Opr.)



S-10080

INPUT WAVEFORM



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